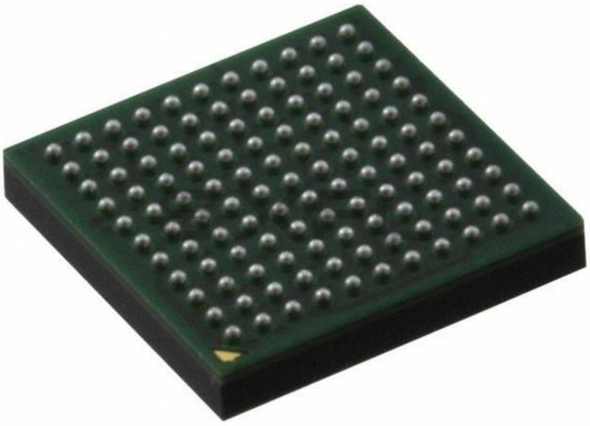

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	50MHz
Connectivity	I²C, IrDA, SPI, UART/USART, USB, USB OTG
Peripherals	DMA, I²S, LVD, POR, PWM, WDT
Number of I/O	56
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 20x16b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	121-LFBGA
Supplier Device Package	121-MAPBGA (8x8)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mk22dx256vmc5

1 Ordering parts

1.1 Determining valid orderable parts

Valid orderable part numbers are provided on the web. To determine the orderable part numbers for this device, go to freescale.com and perform a part number search for the following device numbers: PK22 and MK22 .

2 Part identification

2.1 Description

Part numbers for the chip have fields that identify the specific part. You can use the values of these fields to determine the specific part you have received.

2.2 Format

Part numbers for this device have the following format:

Q K## A M FFF R T PP CC N

2.3 Fields

This table lists the possible values for each field in the part number (not all combinations are valid):

Field	Description	Values
Q	Qualification status	• M = Fully qualified, general market flow • P = Prequalification
K##	Kinetis family	• K22
A	Key attribute	• D = Cortex-M4 w/ DSP • F = Cortex-M4 w/ DSP and FPU
M	Flash memory type	• N = Program flash only • X = Program flash and FlexMemory

Table continues on the next page...

3.2 Definition: Operating behavior

An *operating behavior* is a specified value or range of values for a technical characteristic that are guaranteed during operation if you meet the operating requirements and any other specified conditions.

3.2.1 Example

This is an example of an operating behavior:

Symbol	Description	Min.	Max.	Unit
I_{WP}	Digital I/O weak pullup/ pulldown current	10	130	µA

3.3 Definition: Attribute

An *attribute* is a specified value or range of values for a technical characteristic that are guaranteed, regardless of whether you meet the operating requirements.

3.3.1 Example

This is an example of an attribute:

Symbol	Description	Min.	Max.	Unit
CIN_D	Input capacitance: digital pins	—	7	pF

3.4 Definition: Rating

A *rating* is a minimum or maximum value of a technical characteristic that, if exceeded, may cause permanent chip failure:

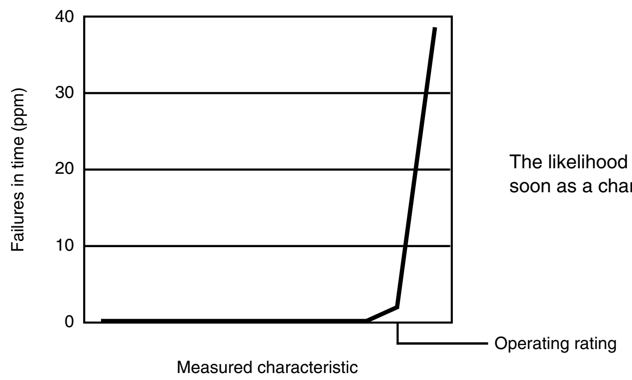
- *Operating ratings* apply during operation of the chip.
- *Handling ratings* apply when the chip is not powered.

3.4.1 Example

This is an example of an operating rating:

Symbol	Description	Min.	Max.	Unit
V_{DD}	1.0 V core supply voltage	–0.3	1.2	V

3.5 Result of exceeding a rating



The likelihood of permanent chip failure increases rapidly as soon as a characteristic begins to exceed one of its operating ratings.

3.6 Relationship between ratings and operating requirements

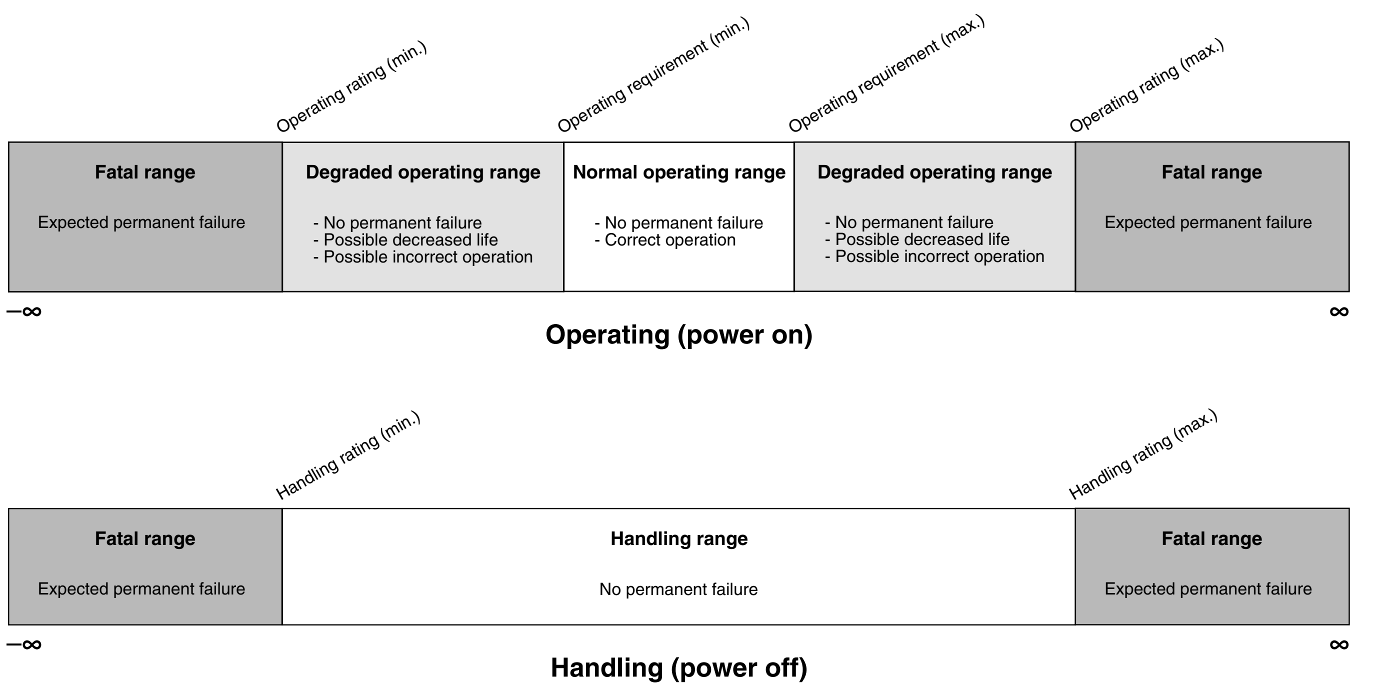


Table 6. Power consumption operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DD_VLLS1}	Very low-leakage stop mode 1 current at 3.0 V • @ –40 to 25°C • @ 50°C • @ 70°C • @ 105°C	—	1.03 1.92 4.03 17.43	1.8 7.5 15.9 28.7	μA	
I_{DD_VLLS0}	Very low-leakage stop mode 0 current at 3.0 V with POR detect circuit enabled • @ –40 to 25°C • @ 50°C • @ 70°C • @ 105°C	—	0.543 1.36 3.39 16.52	1.1 7.58 14.3 24.1	μA	
I_{DD_VLLS0}	Very low-leakage stop mode 0 current at 3.0 V with POR detect circuit disabled • @ –40 to 25°C • @ 50°C • @ 70°C • @ 105°C	—	0.359 1.03 2.87 15.20	0.95 6.8 15.4 25.3	μA	
I_{DD_VBAT}	Average current when CPU is not accessing RTC registers at 3.0 V • @ –40 to 25°C • @ 50°C • @ 70°C • @ 105°C	—	0.91 1.1 1.5 4.3	1.1 1.35 1.85 5.7	μA	9

1. The analog supply current is the sum of the active or disabled current for each of the analog modules on the device. See each module's specification for its supply current.
2. 50 MHz core and system clock, 25 MHz bus clock, and 25 MHz flash clock. MCG configured for FEI mode. All peripheral clocks disabled.
3. 50 MHz core and system clock, 25 MHz bus clock, and 25 MHz flash clock. MCG configured for FEI mode. All peripheral clocks enabled, and peripherals are in active operation.
4. Max values are measured with CPU executing DSP instructions
5. 25 MHz core and system clock, 25 MHz bus clock, and 12.5 MHz flash clock. MCG configured for FEI mode.
6. 4 MHz core, system, and bus clock and 1 MHz flash clock. MCG configured for BLPE mode. All peripheral clocks disabled. Code executing from flash.
7. 4 MHz core, system, and bus clock and 1 MHz flash clock. MCG configured for BLPE mode. All peripheral clocks enabled but peripherals are not in active operation. Code executing from flash.
8. 4 MHz core, system, and bus clock and 1 MHz flash clock. MCG configured for BLPE mode. All peripheral clocks disabled.
9. Includes 32 kHz oscillator current and RTC operation.

5.2.5.1 Diagram: Typical IDD_RUN operating behavior

The following data was measured under these conditions:

- MCG in FBE mode
- USB regulator disabled
- No GPIOs toggled
- Code execution from flash with cache enabled
- For the ALLOFF curve, all peripheral clocks are disabled except FTFL

Table 9. Device clock specifications (continued)

Symbol	Description	Min.	Max.	Unit	Notes
f_{LPTMR_ERCLK}	LPTMR external reference clock	—	16	MHz	
f_{I2S_MCLK}	I2S master clock	—	12.5	MHz	
f_{I2S_BCLK}	I2S bit clock	—	4	MHz	

1. The frequency limitations in VLPR mode here override any frequency specification listed in the timing specification for any other module.

5.3.2 General switching specifications

These general purpose specifications apply to all pins configured for:

- GPIO signaling
- Other peripheral module signaling not explicitly stated elsewhere

Table 10. General switching specifications

Symbol	Description	Min.	Max.	Unit	Notes
	GPIO pin interrupt pulse width (digital glitch filter disabled) — Synchronous path	1.5	—	Bus clock cycles	1, 2
	GPIO pin interrupt pulse width (digital glitch filter disabled, analog filter enabled) — Asynchronous path	100	—	ns	3
	GPIO pin interrupt pulse width (digital glitch filter disabled, analog filter disabled) — Asynchronous path	50	—	ns	3
	External reset pulse width (digital glitch filter disabled)	100	—	ns	3
	Port rise and fall time (high drive strength)				4
	• Slew disabled				
	• $1.71 \le V_{DD} \le 2.7V$	—	13	ns	
	• $2.7 \le V_{DD} \le 3.6V$	—	7	ns	
	• Slew enabled				
	• $1.71 \le V_{DD} \le 2.7V$	—	36	ns	
	• $2.7 \le V_{DD} \le 3.6V$	—	24	ns	
	Port rise and fall time (low drive strength)				5
	• Slew disabled				
	• $1.71 \le V_{DD} \le 2.7V$	—	12	ns	
	• $2.7 \le V_{DD} \le 3.6V$	—	6	ns	
	• Slew enabled				
	• $1.71 \le V_{DD} \le 2.7V$	—	36	ns	
	• $2.7 \le V_{DD} \le 3.6V$	—	24	ns	

1. This is the minimum pulse width that is guaranteed to pass through the pin synchronization circuitry. Shorter pulses may or may not be recognized. In Stop, VLPS, LLS, and VLLSx modes, the synchronizer is bypassed so shorter pulses can be recognized in that case.
2. The greater synchronous and asynchronous timing must be met.

Table 12. JTAG limited voltage range electricals (continued)

Symbol	Description	Min.	Max.	Unit
J5	Boundary scan input data setup time to TCLK rise	20	—	ns
J6	Boundary scan input data hold time after TCLK rise	0	—	ns
J7	TCLK low to boundary scan output data valid	—	25	ns
J8	TCLK low to boundary scan output high-Z	—	25	ns
J9	TMS, TDI input data setup time to TCLK rise	8	—	ns
J10	TMS, TDI input data hold time after TCLK rise	1	—	ns
J11	TCLK low to TDO data valid	—	17	ns
J12	TCLK low to TDO high-Z	—	17	ns
J13	$\overline{\text{TRST}}$ assert time	100	—	ns
J14	$\overline{\text{TRST}}$ setup time (negation) to TCLK high	8	—	ns

Table 13. JTAG full voltage range electricals

Symbol	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
J1	TCLK frequency of operation			MHz
	• Boundary Scan	0	10	
	• JTAG and CJTAG	0	20	
	• Serial Wire Debug	0	40	
J2	TCLK cycle period	1/J1	—	ns
J3	TCLK clock pulse width			
	• Boundary Scan	50	—	ns
	• JTAG and CJTAG	25	—	ns
	• Serial Wire Debug	12.5	—	ns
J4	TCLK rise and fall times	—	3	ns
J5	Boundary scan input data setup time to TCLK rise	20	—	ns
J6	Boundary scan input data hold time after TCLK rise	0	—	ns
J7	TCLK low to boundary scan output data valid	—	25	ns
J8	TCLK low to boundary scan output high-Z	—	25	ns
J9	TMS, TDI input data setup time to TCLK rise	8	—	ns
J10	TMS, TDI input data hold time after TCLK rise	1.4	—	ns
J11	TCLK low to TDO data valid	—	22.1	ns
J12	TCLK low to TDO high-Z	—	22.1	ns
J13	$\overline{\text{TRST}}$ assert time	100	—	ns
J14	$\overline{\text{TRST}}$ setup time (negation) to TCLK high	8	—	ns

Table 20. Flash command timing specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
	Swap Control execution time					
$t_{swapx01}$	• control code 0x01	—	200	—	μs	
$t_{swapx02}$	• control code 0x02	—	70	150	μs	
$t_{swapx04}$	• control code 0x04	—	70	150	μs	
$t_{swapx08}$	• control code 0x08	—	—	30	μs	
	Program Partition for EEPROM execution time					
$t_{pgmpart64k}$	• 64 KB FlexNVM	—	138	—	ms	
	Set FlexRAM Function execution time:					
$t_{setramff}$	• Control Code 0xFF	—	70	—	μs	
$t_{setram32k}$	• 32 KB EEPROM backup	—	0.8	1.2	ms	
$t_{setram64k}$	• 64 KB EEPROM backup	—	1.3	1.9	ms	
Byte-write to FlexRAM for EEPROM operation						
$t_{eewr8bers}$	Byte-write to erased FlexRAM location execution time	—	175	260	μs	3
	Byte-write to FlexRAM execution time:					
$t_{eewr8b32k}$	• 32 KB EEPROM backup	—	385	1800	μs	
$t_{eewr8b64k}$	• 64 KB EEPROM backup		475	2000	μs	
Word-write to FlexRAM for EEPROM operation						
$t_{eewr16bers}$	Word-write to erased FlexRAM location execution time	—	175	260	μs	
	Word-write to FlexRAM execution time:					
$t_{eewr16b32k}$	• 32 KB EEPROM backup	—	385	1800	μs	
$t_{eewr16b64k}$	• 64 KB EEPROM backup	—	475	2000	μs	
Longword-write to FlexRAM for EEPROM operation						
$t_{eewr32bers}$	Longword-write to erased FlexRAM location execution time	—	360	540	μs	
	Longword-write to FlexRAM execution time:					
$t_{eewr32b32k}$	• 32 KB EEPROM backup	—	630	2050	μs	
$t_{eewr32b64k}$	• 64 KB EEPROM backup	—	810	2250	μs	

1. Assumes 25 MHz flash clock frequency.
2. Maximum times for erase parameters based on expectations at cycling end-of-life.
3. For byte-writes to an erased FlexRAM location, the aligned word containing the byte must be erased.

6.4.2 EzPort switching specifications

Table 23. EzPort switching specifications

Num	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
EP1	EZP_CK frequency of operation (all commands except READ)	—	$f_{SYS}/2$	MHz
EP1a	EZP_CK frequency of operation (READ command)	—	$f_{SYS}/8$	MHz
EP2	$\overline{EZP\_CS}$ negation to next $\overline{EZP\_CS}$ assertion	2 x t_{EZP_CK}	—	ns
EP3	$\overline{EZP\_CS}$ input valid to EZP_CK high (setup)	5	—	ns
EP4	EZP_CK high to $\overline{EZP\_CS}$ input invalid (hold)	5	—	ns
EP5	EZP_D input valid to EZP_CK high (setup)	2	—	ns
EP6	EZP_CK high to EZP_D input invalid (hold)	5	—	ns
EP7	EZP_CK low to EZP_Q output valid	—		ns
EP8	EZP_CK low to EZP_Q output invalid (hold)	0	—	ns
EP9	$\overline{EZP\_CS}$ negation to EZP_Q tri-state	—	12	ns

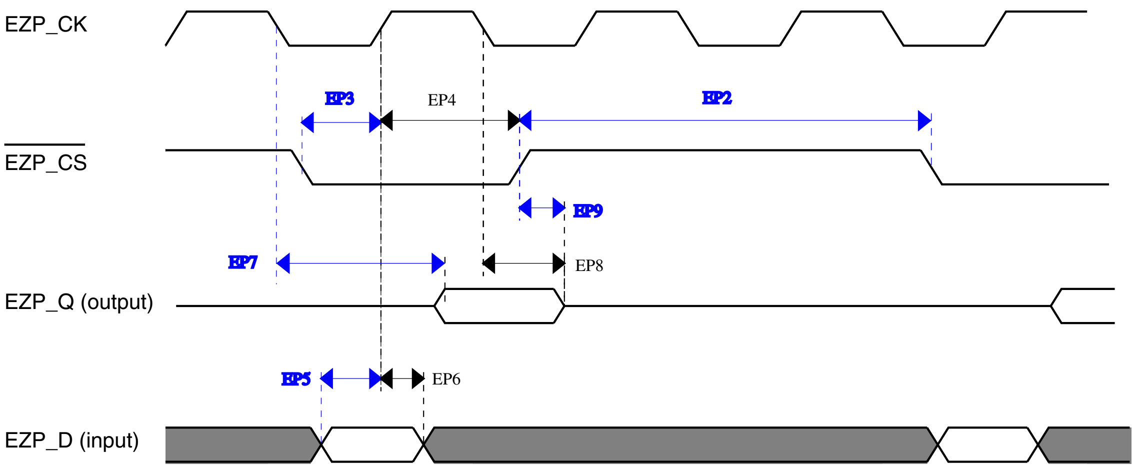


Figure 8. EzPort Timing Diagram

6.5 Security and integrity modules

There are no specifications necessary for the device's security and integrity modules.

6.6 Analog

6.6.1 ADC electrical specifications

The 16-bit accuracy specifications listed in Table 24 and Table 25 are achievable on the differential pins ADCx_DP0, ADCx_DM0.

All other ADC channels meet the 13-bit differential/12-bit single-ended accuracy specifications.

6.6.1.1 16-bit ADC operating conditions

Table 24. 16-bit ADC operating conditions

Symbol	Description	Conditions	Min.	Typ.[1]	Max.	Unit	Notes
V_{DDA}	Supply voltage	Absolute	1.71	—	3.6	V	
ΔV_{DDA}	Supply voltage	Delta to V_{DD} ($V_{DD} – V_{DDA}$)	-100	0	+100	mV	2
ΔV_{SSA}	Ground voltage	Delta to V_{SS} ($V_{SS} – V_{SSA}$)	-100	0	+100	mV	2
V_{REFH}	ADC reference voltage high		1.13	V_{DDA}	V_{DDA}	V	
V_{REFL}	ADC reference voltage low		V_{SSA}	V_{SSA}	V_{SSA}	V	
V_{ADIN}	Input voltage	• 16-bit differential mode • All other modes	VREFL VREFL	— —	31/32 * VREFH VREFH	V	
C_{ADIN}	Input capacitance	• 16-bit mode • 8-bit / 10-bit / 12-bit modes	— —	8 4	10 5	pF	
R_{ADIN}	Input resistance		—	2	5	kΩ	
R_{AS}	Analog source resistance	13-bit / 12-bit modes f_{ADCK} < 4 MHz	—	—	5	kΩ	3
f_{ADCK}	ADC conversion clock frequency	≤ 13-bit mode	1.0	—	18.0	MHz	4
f_{ADCK}	ADC conversion clock frequency	16-bit mode	2.0	—	12.0	MHz	4
C_{rate}	ADC conversion rate	≤ 13-bit modes No ADC hardware averaging Continuous conversions enabled, subsequent conversion time	20.000	—	818.330	Ksps	5
C_{rate}	ADC conversion rate	16-bit mode No ADC hardware averaging Continuous conversions enabled, subsequent conversion time	37.037	—	461.467	Ksps	5

1. Typical values assume V_{DDA} = 3.0 V, Temp = 25 °C, f_{ADCK} = 1.0 MHz, unless otherwise stated. Typical values are for reference only, and are not tested in production.
2. DC potential difference.
3. This resistance is external to MCU. To achieve the best results, the analog source resistance must be kept as low as possible. The results in this data sheet were derived from a system that had < 8 Ω analog source resistance. The R_{AS}/C_{AS} time constant should be kept to < 1 ns.
4. To use the maximum ADC conversion clock frequency, CFG2[ADHSC] must be set and CFG1[ADLPC] must be clear.
5. For guidelines and examples of conversion rate calculation, download the ADC calculator tool.

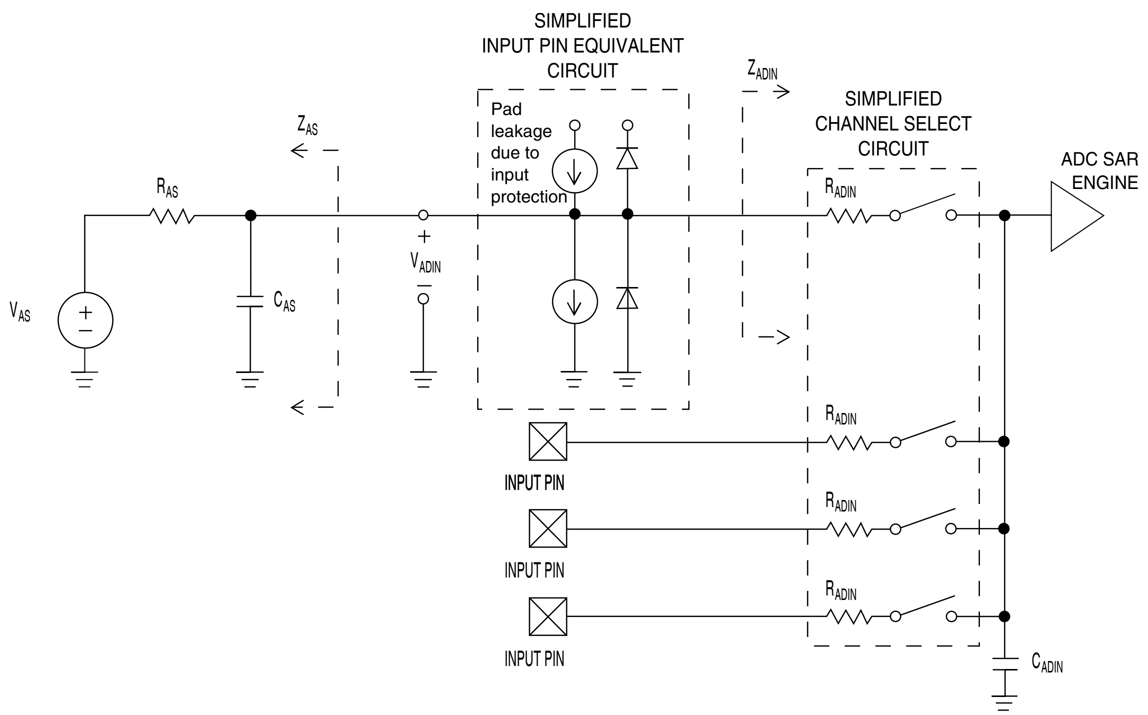


Figure 9. ADC input impedance equivalency diagram

6.6.1.2 16-bit ADC electrical characteristics

Table 25. 16-bit ADC characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$)

Symbol	Description	Conditions[1].	Min.	Typ.[2]	Max.	Unit	Notes
I_{DDA_ADC}	Supply current		0.215	—	1.7	mA	3
f_{ADACK}	ADC asynchronous clock source	• ADLPC = 1, ADHSC = 0 • ADLPC = 1, ADHSC = 1 • ADLPC = 0, ADHSC = 0 • ADLPC = 0, ADHSC = 1	1.2 2.4 3.0 4.4	2.4 4.0 5.2 6.2	3.9 6.1 7.3 9.5	MHz MHz MHz MHz	$t_{ADACK} = 1/f_{ADACK}$
	Sample Time	See Reference Manual chapter for sample times					
TUE	Total unadjusted error	• 12-bit modes • <12-bit modes	— —	±4 ±1.4	±6.8 ±2.1	LSB[4]	5
DNL	Differential non-linearity	• 12-bit modes • <12-bit modes	— —	±0.7 ±0.2	-1.1 to +1.9 -0.3 to 0.5	LSB[4]	5

Table continues on the next page...

2. Typical values assume V_{DDA} = 3.0 V, Temp = 25 °C, f_{ADCK} = 2.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.
3. The ADC supply current depends on the ADC conversion clock speed, conversion rate and ADC_CFG1[ADLPC] (low power). For lowest power operation, ADC_CFG1[ADLPC] must be set, the ADC_CFG2[ADHSC] bit must be clear with 1 MHz ADC conversion clock speed.
4. 1 LSB = $(V_{REFH} - V_{REFL})/2^N$
5. ADC conversion clock < 16 MHz, Max hardware averaging (AVGE = %1, AVGS = %11)
6. Input data is 100 Hz sine wave. ADC conversion clock < 12 MHz.
7. Input data is 1 kHz sine wave. ADC conversion clock < 12 MHz.
8. ADC conversion clock < 3 MHz

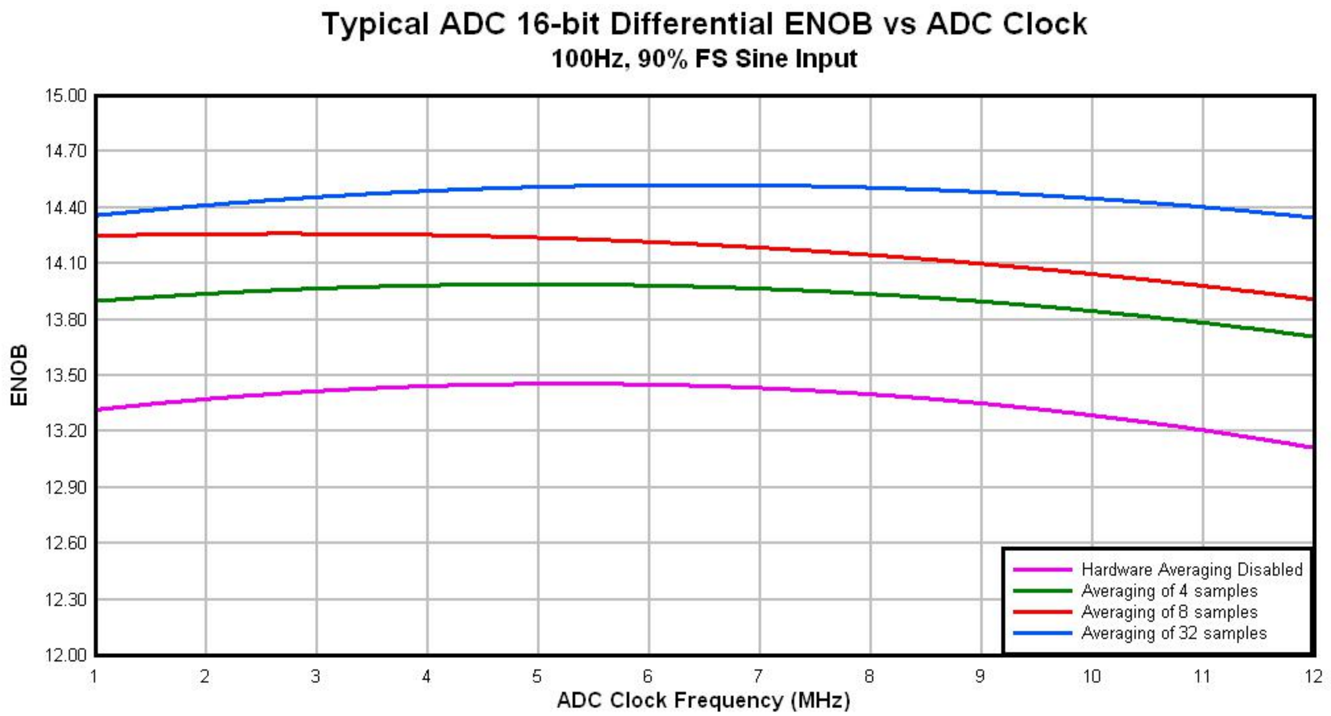


Figure 10. Typical ENOB vs. ADC_CLK for 16-bit differential mode

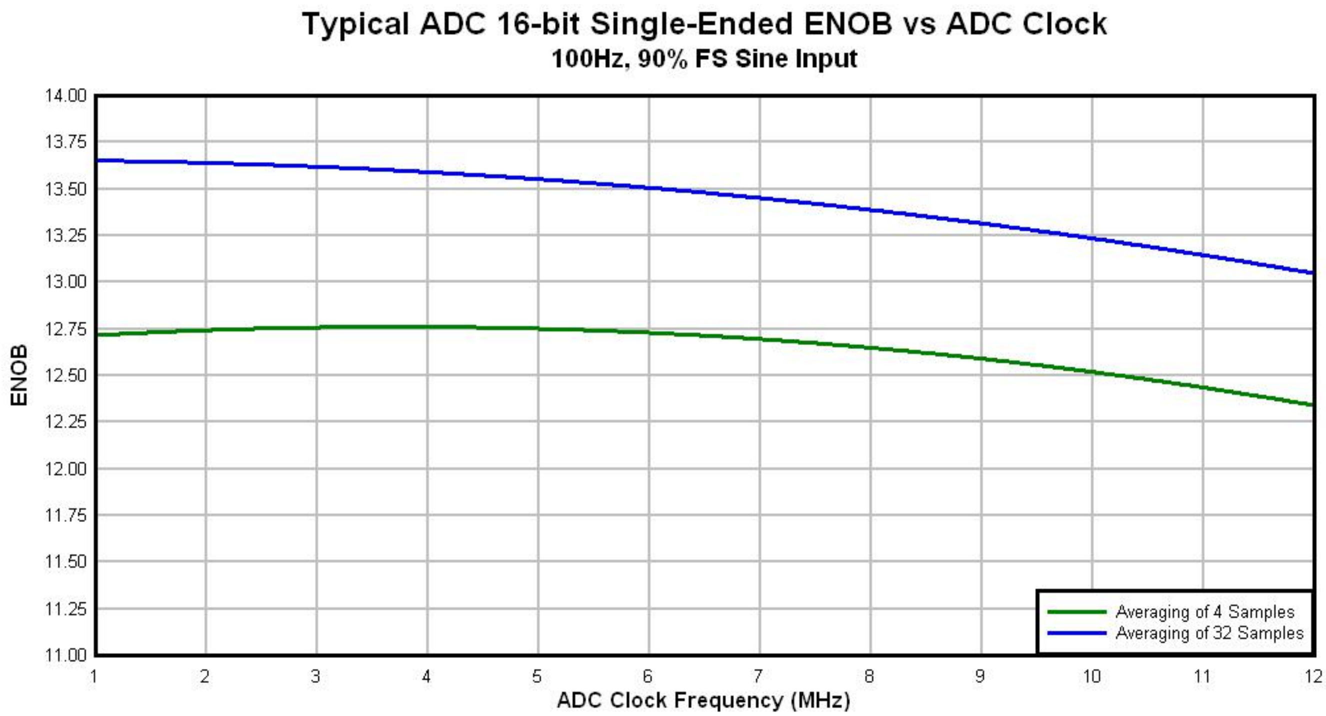


Figure 11. Typical ENOB vs. ADC_CLK for 16-bit single-ended mode

6.6.2 CMP and 6-bit DAC electrical specifications

Table 26. Comparator and 6-bit DAC electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit
V_{DD}	Supply voltage	1.71	—	3.6	V
I_{DDHS}	Supply current, High-speed mode (EN=1, PMODE=1)	—	—	200	μA
I_{DDLS}	Supply current, low-speed mode (EN=1, PMODE=0)	—	—	20	μA
V_{AIN}	Analog input voltage	V_{SS} – 0.3	—	V_{DD}	V
V_{AIO}	Analog input offset voltage	—	—	20	mV
V_H	Analog comparator hysteresis[1]				
	• CR0[HYSTCTR] = 00	—	5	—	mV
	• CR0[HYSTCTR] = 01	—	10	—	mV
	• CR0[HYSTCTR] = 10	—	20	—	mV
	• CR0[HYSTCTR] = 11	—	30	—	mV
V_{CMPOh}	Output high	V_{DD} – 0.5	—	—	V
V_{CMPOl}	Output low	—	—	0.5	V
t_{DHS}	Propagation delay, high-speed mode (EN=1, PMODE=1)	20	50	200	ns
t_{DLS}	Propagation delay, low-speed mode (EN=1, PMODE=0)	80	250	600	ns
	Analog comparator initialization delay[2]	—	—	40	μs

Table continues on the next page...

Table 26. Comparator and 6-bit DAC electrical specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit
I_{DAC6b}	6-bit DAC current adder (enabled)	—	7	—	μA
INL	6-bit DAC integral non-linearity	–0.5	—	0.5	LSB[3]
DNL	6-bit DAC differential non-linearity	–0.3	—	0.3	LSB

1. Typical hysteresis is measured with input voltage range limited to 0.6 to V_{DD}–0.6 V.
2. Comparator initialization delay is defined as the time between software writes to change control inputs (Writes to CMP_DACCR[DACEN], CMP_DACCR[VRSEL], CMP_DACCR[VOSEL], CMP_MUXCR[PSEL], and CMP_MUXCR[MSEL]) and the comparator output settling to a stable level.
3. 1 LSB = $V_{reference}$/64

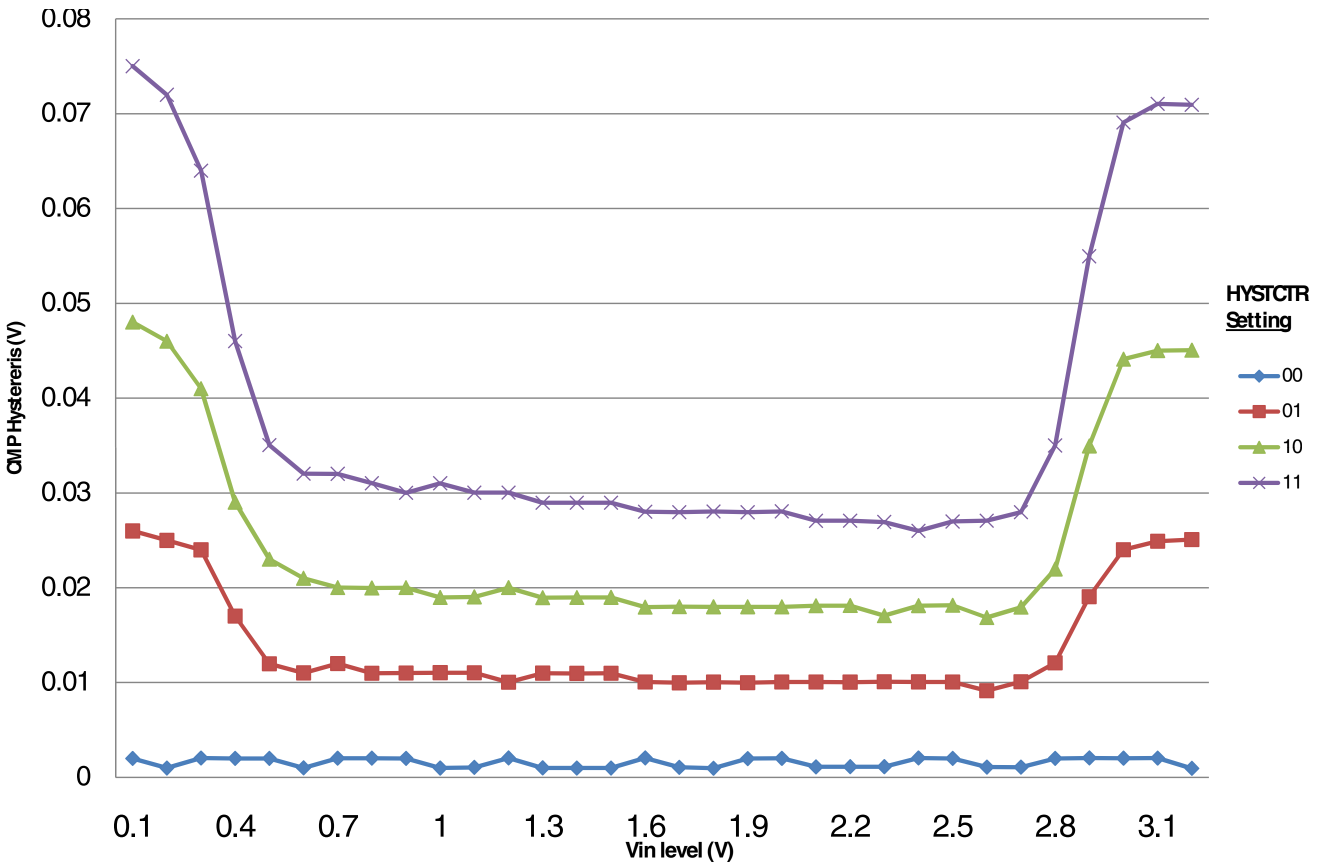


Figure 12. Typical hysteresis vs. Vin level (VDD = 3.3 V, PMODE = 0)

6.6.3.2 12-bit DAC operating behaviors

Table 28. 12-bit DAC operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DDA_DACLP}	Supply current — low-power mode	—	—	330	μA	
I_{DDA_DACHP}	Supply current — high-speed mode	—	—	1200	μA	
t_{DACLP}	Full-scale settling time (0x080 to 0xF7F) — low-power mode	—	100	200	μs	1
t_{DACHP}	Full-scale settling time (0x080 to 0xF7F) — high-power mode	—	15	30	μs	1
$t_{CCDACLP}$	Code-to-code settling time (0xBF8 to 0xC08) — low-power mode and high-speed mode	—	0.7	1	μs	1
$V_{dacoutl}$	DAC output voltage range low — high-speed mode, no load, DAC set to 0x000	—	—	100	mV	
$V_{dacouth}$	DAC output voltage range high — high-speed mode, no load, DAC set to 0xFFF	V_{DACR} −100	—	V_{DACR}	mV	
INL	Integral non-linearity error — high speed mode	—	—	±8	LSB	2
DNL	Differential non-linearity error — V_{DACR} > 2 V	—	—	±1	LSB	3
DNL	Differential non-linearity error — V_{DACR} = VREF_OUT	—	—	±1	LSB	4
V_{OFFSET}	Offset error	—	±0.4	±0.8	%FSR	5
E_G	Gain error	—	±0.1	±0.6	%FSR	5
PSRR	Power supply rejection ratio, V_{DDA} ≥ 2.4 V	60	—	90	dB	
T_{CO}	Temperature coefficient offset voltage	—	3.7	—	μV/C	6
T_{GE}	Temperature coefficient gain error	—	0.000421	—	%FSR/C	
Rop	Output resistance (load = 3 kΩ)	—	—	250	Ω	
SR	Slew rate -80h→ F7Fh→ 80h				V/μs	
	• High power (SP_{HP})	1.2	1.7	—		
	• Low power (SP_{LP})	0.05	0.12	—		
CT	Channel to channel cross talk	—	—	-80	dB	
BW	3dB bandwidth				kHz	
	• High power (SP_{HP})	550	—	—		
	• Low power (SP_{LP})	40	—	—		

1. Settling within ±1 LSB
2. The INL is measured for 0 + 100 mV to V_{DACR} −100 mV
3. The DNL is measured for 0 + 100 mV to V_{DACR} −100 mV
4. The DNL is measured for 0 + 100 mV to V_{DACR} −100 mV with V_{DDA} > 2.4 V
5. Calculated by a best fit curve from V_{SS} + 100 mV to V_{DACR} − 100 mV
6. V_{DDA} = 3.0 V, reference select set for V_{DDA} (DACx_CO:DACRFS = 1), high power mode (DACx_C0:LPEN = 0), DAC set to 0x800, temperature range is across the full range of the device

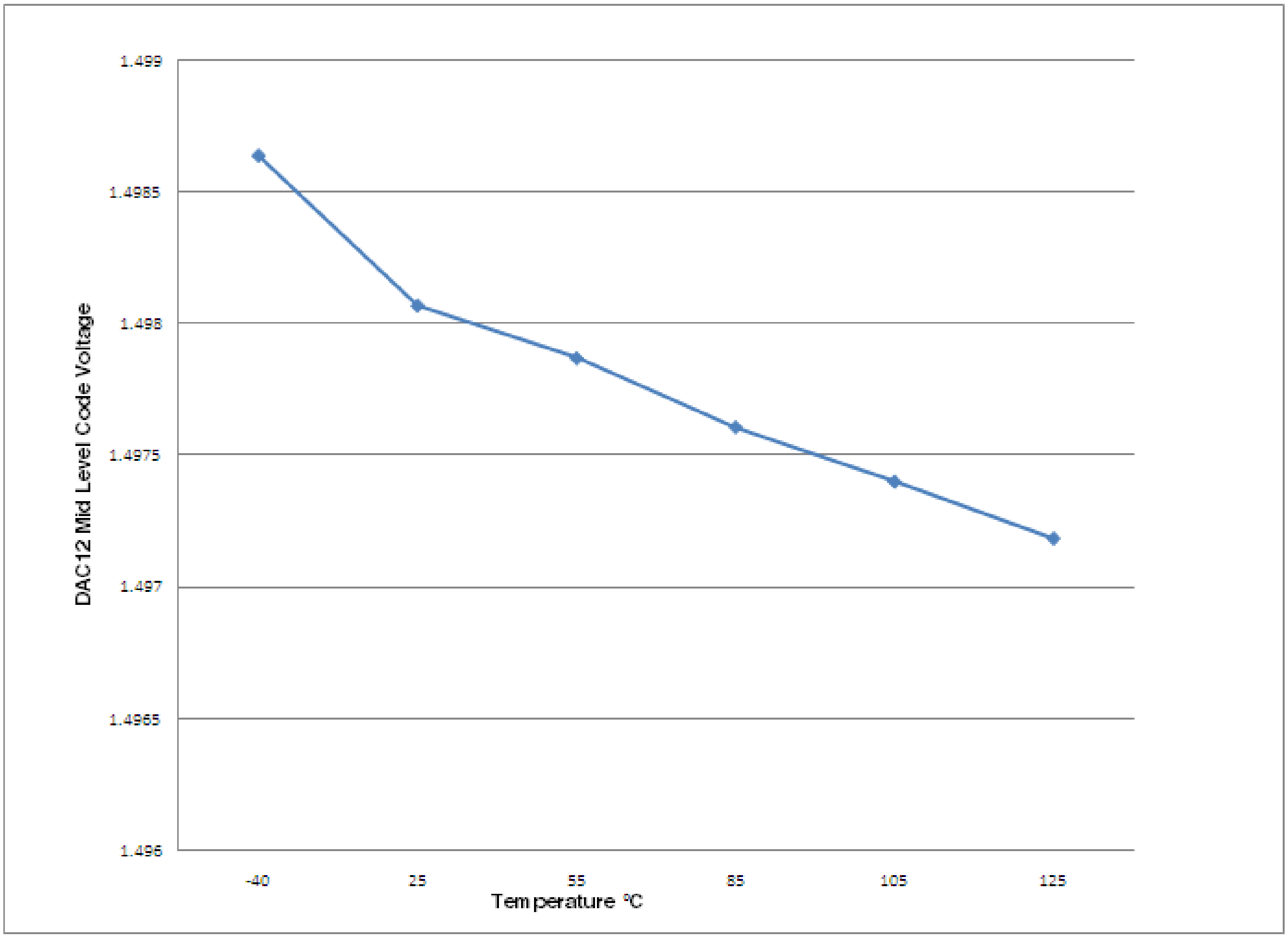


Figure 15. Offset at half scale vs. temperature

6.6.4 Voltage reference electrical specifications

Table 29. VREF full-range operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
V_{DDA}	Supply voltage	1.71	3.6	V	
T_A	Temperature	Operating temperature range of the device		°C	
C_L	Output load capacitance	100		nF	1, 2

1. C_L must be connected to VREF_OUT if the VREF_OUT functionality is being used for either an internal or external reference.
2. The load capacitance should not exceed +/-25% of the nominal specified C_L value over the operating temperature range of the device.

6.8.1 USB electrical specifications

The USB electricals for the USB On-the-Go module conform to the standards documented by the Universal Serial Bus Implementers Forum. For the most up-to-date standards, visit usb.org.

6.8.2 USB DCD electrical specifications

Table 33. USB DCD electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit
V_{DP_SRC}	USB_DP source voltage (up to 250 μA)	0.5	—	0.7	V
V_{LGC}	Threshold voltage for logic high	0.8	—	2.0	V
I_{DP_SRC}	USB_DP source current	7	10	13	μA
I_{DM_SINK}	USB_DM sink current	50	100	150	μA
R_{DM_DWN}	D- pulldown resistance for data pin contact detect	14.25	—	24.8	kΩ
V_{DAT_REF}	Data detect voltage	0.25	0.33	0.4	V

6.8.3 VREG electrical specifications

Table 34. VREG electrical specifications

Symbol	Description	Min.	Typ.[1]	Max.	Unit	Notes
VREGIN	Input supply voltage	2.7	—	5.5	V	
I_{DDon}	Quiescent current — Run mode, load current equal zero, input supply (VREGIN) > 3.6 V	—	125	186	μA	
I_{DDstby}	Quiescent current — Standby mode, load current equal zero	—	1.1	10	μA	
I_{DDoff}	Quiescent current — Shutdown mode • VREGIN = 5.0 V and temperature=25 °C • Across operating voltage and temperature	 — —	 650 —	 — 4	 nA μA	
$I_{LOADstby}$	Maximum load current — Standby mode	—	—	1	mA	
$V_{Reg33out}$	Regulator output voltage — Input supply (VREGIN) > 3.6 V • Run mode • Standby mode	 3 2.1	 3.3 2.8	 3.6 3.6	 V V	
$V_{Reg33out}$	Regulator output voltage — Input supply (VREGIN) < 3.6 V, pass-through mode	2.1	—	3.6	V	2
C_{OUT}	External output capacitor	1.76	2.2	8.16	μF	
ESR	External output capacitor equivalent series resistance	1	—	100	mΩ	
I_{LIM}	Short circuit current	—	315	—	mA	

1. Typical values assume VREGIN = 5.0 V, Temp = 25 °C unless otherwise stated.
2. Operating in pass-through mode: regulator output voltage equal to the input voltage minus a drop proportional to I_{Load}.

6.8.4 DSPI switching specifications (limited voltage range)

The DMA Serial Peripheral Interface (DSPI) provides a synchronous serial bus with master and slave operations. Many of the transfer attributes are programmable. The tables below provide DSPI timing characteristics for classic SPI timing modes. Refer to the DSPI chapter of the Reference Manual for information on the modified transfer formats used for communicating with slower peripheral devices.

Table 35. Master mode DSPI timing (limited voltage range)

Num	Description	Min.	Max.	Unit	Notes
	Operating voltage	2.7	3.6	V	
	Frequency of operation	—	25	MHz	
DS1	DSPI_SCK output cycle time	2 x t_{BUS}	—	ns	
DS2	DSPI_SCK output high/low time	$(t_{SCK}/2) - 2$	$(t_{SCK}/2) + 2$	ns	
DS3	DSPI_PCS*n* valid to DSPI_SCK delay	$(t_{BUS} \times 2) - 2$	—	ns	1
DS4	DSPI_SCK to DSPI_PCS*n* invalid delay	$(t_{BUS} \times 2) - 2$	—	ns	2
DS5	DSPI_SCK to DSPI_SOUT valid	—	8.5	ns	
DS6	DSPI_SCK to DSPI_SOUT invalid	–2	—	ns	
DS7	DSPI_SIN to DSPI_SCK input setup	15	—	ns	
DS8	DSPI_SCK to DSPI_SIN input hold	0	—	ns	

1. The delay is programmable in SPIx_CTARn[PSSCK] and SPIx_CTARn[CSSCK].
2. The delay is programmable in SPIx_CTARn[PASC] and SPIx_CTARn[ASC].

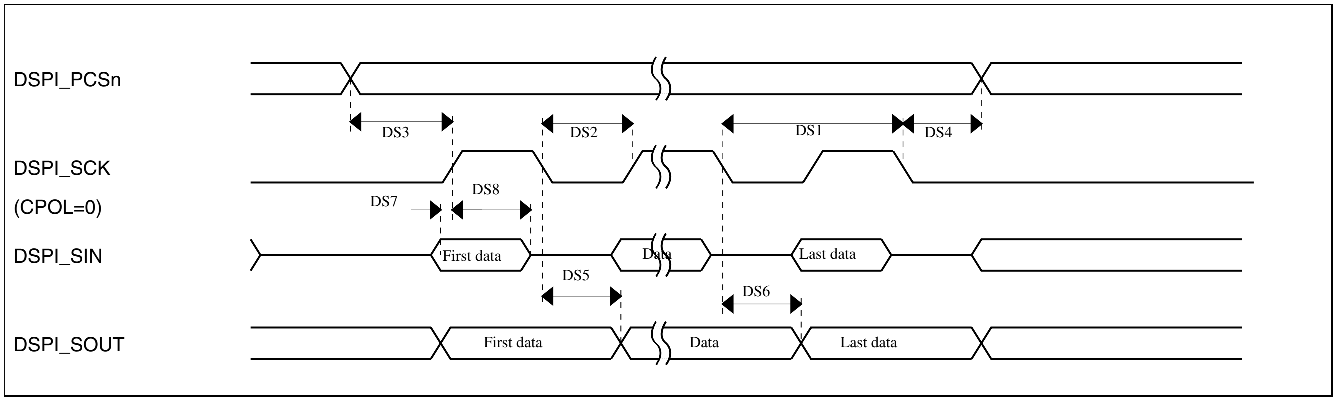


Figure 16. DSPI classic SPI timing — master mode

NOTE

- The analog input signals ADC0_SE10, ADC0_SE11, ADC0_DP1, and ADC0_DM1 are available only for K11, K12, K21, and K22 devices and are not present on K10 and K20 devices.
- The TRACE signals on PTE0, PTE1, PTE2, PTE3, and PTE4 are available only for K11, K12, K21, and K22 devices and are not present on K10 and K20 devices.
- If the VBAT pin is not used, the VBAT pin should be left floating. Do not connect VBAT pin to VSS.
- The FTM_CLKIN signals on PTB16 and PTB17 are available only for K11, K12, K21, and K22 devices and is not present on K10 and K20 devices. For K22D devices this signal is on ALT4, and for K22F devices, this signal is on ALT7.
- The FTM0_CH2 signal on PTC5/LLWU_P9 is available only for K11, K12, K21, and K22 devices and is not present on K10 and K20 devices.
- The I2C0_SCL signal on PTD2/LLWU_P13 and I2C0_SDA signal on PTD3 are available only for K11, K12, K21, and K22 devices and are not present on K10 and K20 devices.

121 MAP BGA	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	EzPort
E4	ADC0_SE10	ADC0_SE10	PTE0	SPI1_PCS1	UART1_TX		TRACE_CLKOUT	I2C1_SDA	RTC_CLKOUT	
E3	ADC0_SE11	ADC0_SE11	PTE1/ LLWU_P0	SPI1_SOUT	UART1_RX		TRACE_D3	I2C1_SCL	SPI1_SIN	
E2	ADC0_DP1	ADC0_DP1	PTE2/ LLWU_P1	SPI1_SCK	UART1_CTS_b		TRACE_D2			
F4	ADC0_DM1	ADC0_DM1	PTE3	SPI1_SIN	UART1_RTS_b		TRACE_D1		SPI1_SOUT	
H7	DISABLED		PTE4/ LLWU_P2	SPI1_PCS0	UART3_TX		TRACE_D0			
G4	DISABLED		PTE5	SPI1_PCS2	UART3_RX					
E6	VDD	VDD								
G7	VSS	VSS								
L6	VSS	VSS								
F1	USB0_DP	USB0_DP								
F2	USB0_DM	USB0_DM								
G1	VOUT33	VOUT33								
G2	VREGIN	VREGIN								
K1	ADC0_DP0	ADC0_DP0								
K2	ADC0_DM0	ADC0_DM0								

121 MAP BGA	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	EzPort
L1	ADC0_DP3	ADC0_DP3								
L2	ADC0_DM3	ADC0_DM3								
F5	VDDA	VDDA								
G5	VREFH	VREFH								
G6	VREFL	VREFL								
F6	VSSA	VSSA								
L3	VREF_OUT/ CMP1_IN5/ CMP0_IN5	VREF_OUT/ CMP1_IN5/ CMP0_IN5								
K5	DAC0_OUT/ CMP1_IN3/ ADC0_SE23	DAC0_OUT/ CMP1_IN3/ ADC0_SE23								
L7	RTC_WAKEUP_ B	RTC_WAKEUP_ B								
L4	XTAL32	XTAL32								
L5	EXTAL32	EXTAL32								
K6	VBAT	VBAT								
J6	JTAG_TCLK/ SWD_CLK/ EZP_CLK		PTA0	UART0_CTS_b/ UART0_COL_b	FTM0_CH5				JTAG_TCLK/ SWD_CLK	EZP_CLK
H8	JTAG_TDI/ EZP_DI		PTA1	UART0_RX	FTM0_CH6				JTAG_TDI	EZP_DI
J7	JTAG_TDO/ TRACE_SWO/ EZP_DO		PTA2	UART0_TX	FTM0_CH7				JTAG_TDO/ TRACE_SWO	EZP_DO
H9	JTAG_TMS/ SWD_DIO		PTA3	UART0_RTS_b	FTM0_CH0				JTAG_TMS/ SWD_DIO	
J8	NMI_b/ EZP_CS_b		PTA4/ LLWU_P3		FTM0_CH1				NMI_b	EZP_CS_b
K7	DISABLED		PTA5	USB_CLKIN	FTM0_CH2			I2S0_TX_BCLK	JTAG_TRST_b	
K8	DISABLED		PTA12		FTM1_CH0			I2S0_TXD0	FTM1_QD_PHA	
L8	DISABLED		PTA13/ LLWU_P4		FTM1_CH1			I2S0_TX_FS	FTM1_QD_PHB	
K9	DISABLED		PTA14	SPI0_PCS0	UART0_TX			I2S0_RX_BCLK	I2S0_TXD1	
L9	DISABLED		PTA15	SPI0_SCK	UART0_RX			I2S0_RXD0		
J10	DISABLED		PTA16	SPI0_SOUT	UART0_CTS_b/ UART0_COL_b			I2S0_RX_FS	I2S0_RXD1	
H10	DISABLED		PTA17	SPI0_SIN	UART0_RTS_b			I2S0_MCLK		
L10	VDD	VDD								
K10	VSS	VSS								
L11	EXTAL0	EXTAL0	PTA18		FTM0_FLT2				FTM_CLKIN0	
K11	XTAL0	XTAL0	PTA19		FTM1_FLT0			LPTMR0_ALT1	FTM_CLKIN1	
J11	RESET_b	RESET_b								
G11	ADC0_SE8	ADC0_SE8	PTB0/ LLWU_P5	I2C0_SCL	FTM1_CH0			FTM1_QD_PHA		

	1	2	3	4	5	6	7	8	9	10	11	
A	PTD7	PTD5	PTD4/ LLWU_P14	NC	NC	PTC13	PTC8	PTC4/ LLWU_P8	NC	NC	NC	A
B	NC	PTD6/ LLWU_P15	PTD3	NC	NC	PTC12	PTC7	PTC3/ LLWU_P7	PTC0	PTB16	PTB12	B
C	NC	NC	PTD2/ LLWU_P13	PTC17	PTC11/ LLWU_P11	PTC10	PTC6/ LLWU_P10	PTC2	PTB19	PTB11	PTB13	C
D	NC	NC	PTD1	PTD0/ LLWU_P12	PTC16	PTC9	PTC5/ LLWU_P9	PTC1/ LLWU_P6	PTB18	PTB10	NC	D
E	NC	PTE2/ LLWU_P1	PTE1/ LLWU_P0	PTE0	VDD	VDD	NC	NC	PTB17	NC	NC	E
F	USB0_DP	USB0_DM	NC	PTE3	VDDA	VSSA	NC	NC	NC	NC	NC	F
G	VOUT33	VREGIN	VSS	PTE5	VREFH	VREFL	VSS	PTB3	PTB2	PTB1	PTB0/ LLWU_P5	G
H	NC	NC	NC	NC	NC	NC	PTE4/ LLWU_P2	PTA1	PTA3	PTA17	NC	H
J	NC	NC	NC	NC	NC	PTA0	PTA2	PTA4/ LLWU_P3	NC	PTA16	RESET_b	J
K	ADC0_DP0	ADC0_DM0	NC	NC	DAC0_OUT/ CMP1_IN3/ ADC0_SE23	VBAT	PTA5	PTA12	PTA14	VSS	PTA19	K
L	ADC0_DP3	ADC0_DM3	VREF_OUT/ CMP1_IN5/ CMP0_IN5	XTAL32	EXTAL32	VSS	RTC_ WAKEUP_B	PTA13/ LLWU_P4	PTA15	VDD	PTA18	L
	1	2	3	4	5	6	7	8	9	10	11	

Figure 24. K22 121 MAPBGA Pinout Diagram

9 Revision History

The following table provides a revision history for this document.

Table 43. Revision History

Rev. No.	Date	Substantial Changes
1	6/2012	Alpha customer release.
1.1	6/2012	In Table 6, "Power consumption operating behaviors", changed the units of I_{DD_VLLS2}, I_{DD_VLLS1}, I_{DD_VLLS0}, and I_{DD_VBAT} from nA to μA.

Table continues on the next page...